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(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: PARK, Stephen, Keetai; 7554 Hollanderray Place, Cupertino, CA 95014 (US). AVANZINO, Steven, C.; 7504 Barnhart Place, Cupertino, CA 95014 (US).

(74) Agent: RODDY, Richard, J.; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

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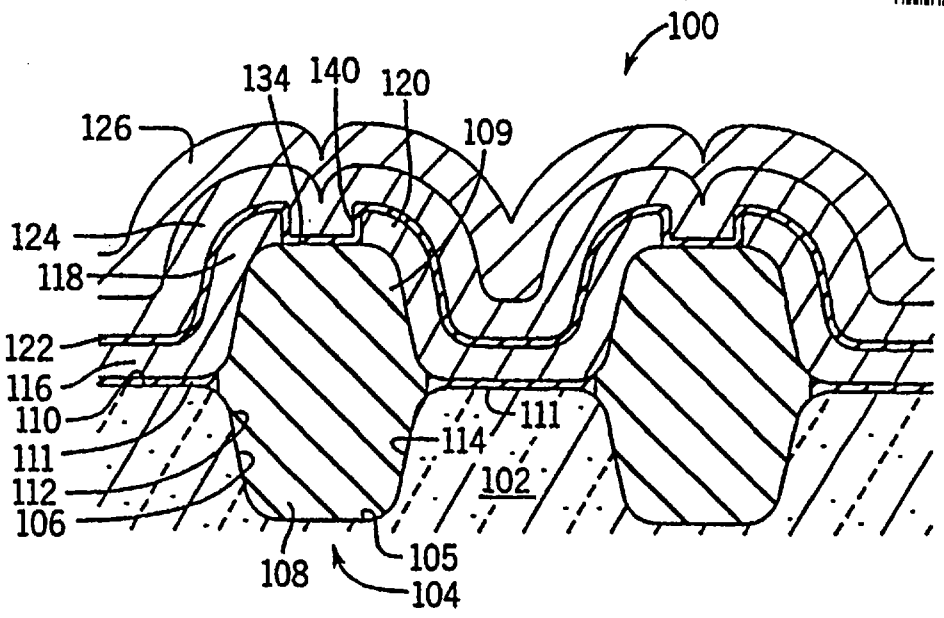
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(54) Title: NONVOLATILE MEMORY HAVING HIGH GATE COUPLING CAPACITANCE

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(57) Abstract: The present invention is directed to an integrated circuit (100) having an increased gate coupling capacitance. The integrated circuit (100) includes a substrate (102) having a surface (110), the substrate (102) having a trench (106) extending below the surface (110). A trench fill material (108) is disposed in the trench (106) and has a portion (109) extending above the surface (110). A first conductive layer (116) is adjacent the trench fill material (108) and has a portion (118) extending over the portion (109) of the trench fill material (108). An insulative layer (122) is above the first conductive layer (116) and a second conductive layer (124) is adjacent the insulative material (122).

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